



Note:

1. SUBSTRATE:IR MONO GRADE SI
2. GROWING METHOD:CZ
3. CLEAR APERTURE:90%
4. SURFACE QUALITY:S1&S2 60-40 SCRATCH-DIG
5. PARALLELISM:3ARCMIN
6. PV: $\lambda/2$
7. COATING:NONE

7 FINE GRIND SURFACE

SPECIFICATIONS SUBJECT TO CHANGE
WITHOUT NOTICE

FOR INFORMATION ONLY
NOT FOR MANUFACTURE

| | | | |
|---------------------------|------------------|-------------|--|
| DRAWING PROJECTION | | ALL DIMS IN | MM |
| DESIGNED | CHECKED | APPROVED | SCALE |
| | | | 1:1 |
| MATERIAL | Silicon | TITLE | SI IR-MONO ROUND WINDOW $\varnothing 25 * T4$ |
| 本征晶体 INTRINSIC CRYSTAL | www.icc-mall.com | DWG NO | PSI01E002 |
| | | EDITION | 1ST |
| | | SHEET | 1/1 |